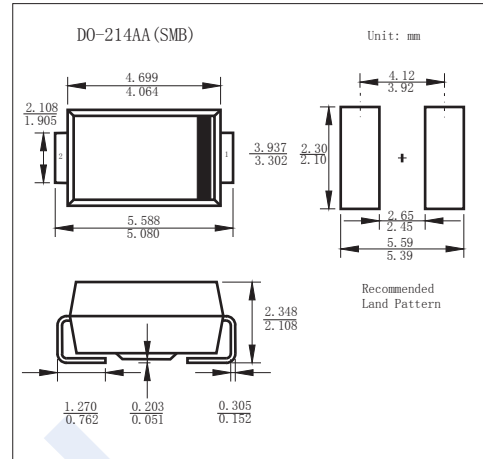


Rectifier Diodes

ES2A ~ ES2D

■ Features

- Glass Passivated Die Construction
- Super-Fast Recovery Time For High Efficiency
- Surge Overload Rating to 50A Peak
- Ideally Suited for Automated Assembly
- Lead Free Finish/RoHS Compliant
- Green Molding Compound

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	ES2A	ES2B	ES2C	ES2D	Unit
Repetitive Peak Reverse Voltage	VRRM	50	100	150	200	V
Working Peak Reverse Voltage	VRWM					
Maximum DC Blocking Voltage	VDC					
RMS Reverse Voltage	VR(RMS)	35	70	105	140	
Forward Voltage @ IF=2A	VF	0.92				A
Averaged Forward Current.TT=110℃	IFAV	2				
Peak Forward Surge Current @ 8.3ms	IFSM	50				
Maximum DC Reverse Current Ta=25℃ Ta=125℃	IR	5 350				μA
Maximum Reverse Current (Note.1)	trr	25				ns
Typical Junction Capacitance (Note.2)	Cj	25				pF
Typical Thermal Resistance, Junction to Terminal	RθJT	20				℃/W
Junction Temperature	Tj	150				℃
Storage Temperature	Tstg	-55 to 150				

Note.1: Measured with $I_F = 0.5\text{ A}$, $I_R = 1\text{ A}$, $t_{rr} = 0.25\text{ A}$

Note.2: Measured at 1MHz and applied reverse voltage of 4V D.C

■ Marking

NO.	ES2A	ES2B	ES2C	ES2D
Marking	ES2A	ES2B	ES2C	ES2D

Rectifier Diodes

ES2A ~ ES2D

■ Typical Characteristics

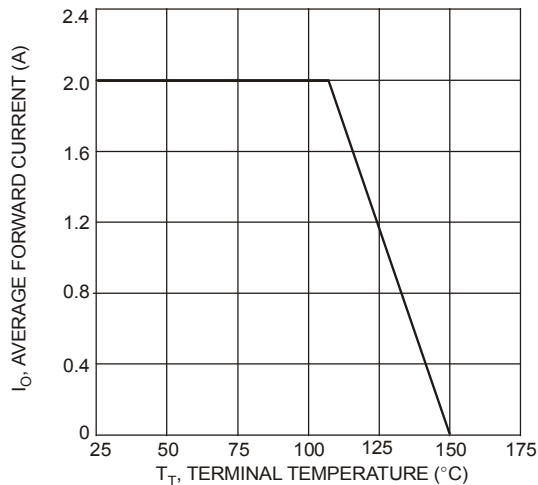


Fig. 1 Forward Current Derating Curve

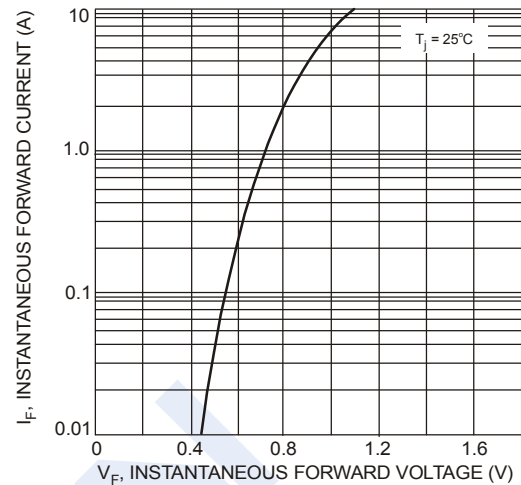


Fig. 2 Typical Forward Characteristics

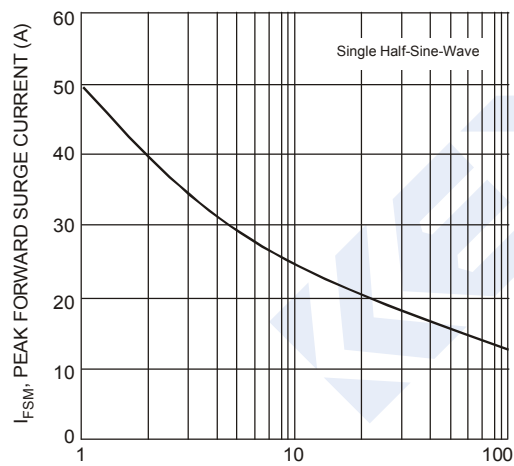


Fig. 3 Surge Current Derating Curve

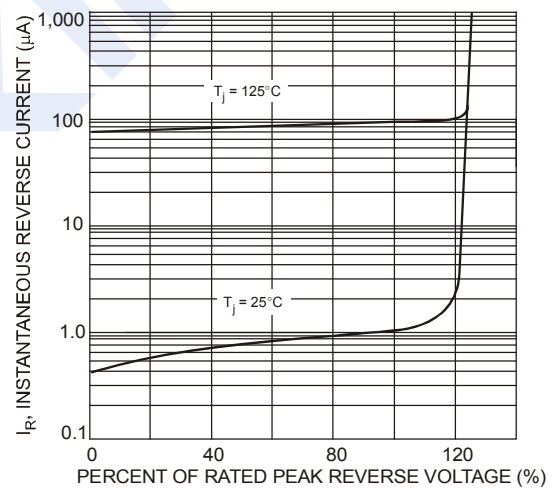
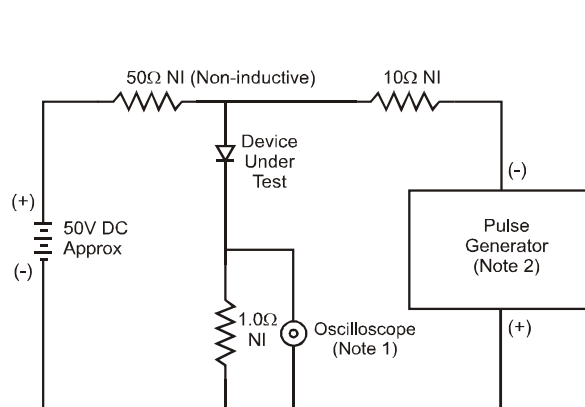


Fig. 4 Typical Reverse Characteristics



Notes:

1. Rise Time = 7.0ns max. Input Impedance = 1.0MΩ, 22pF.
2. Rise Time = 10ns max. Input Impedance = 50Ω.

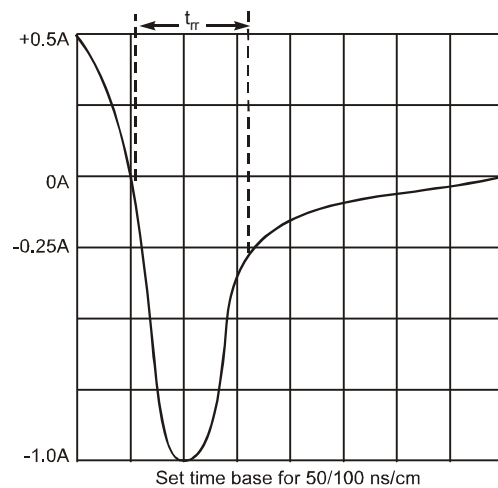


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit